# MC14012B

# **Dual 4-Input NAND Gates**

The MC14012B dual 4-input NAND gates are constructed with P-Channel and N-Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

#### **Features**

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin–for–Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

#### MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.



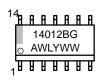
#### ON Semiconductor®

http://onsemi.com



SOIC-14 D SUFFIX CASE 751A

#### MARKING DIAGRAM



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G = Pb-Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### MC14012B

#### MC14012B Dual 4-Input NAND Gate

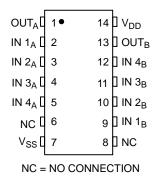


Figure 1. Pin Assignment

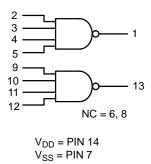


Figure 2. Logic Diagram

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14012BDG	SOIC-14 (Pb-Free)	55 Units / Rail
NLV14012BDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14012BDR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
NLV14012BDR2G*	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### MC14012B

#### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				-55	5°C		25°C		125	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V <sub>in</sub> = 0 or V <sub>DD</sub>	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>IL</sub>	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	_ _ _	Vdc
Output Drive Current $ (V_{OH} = 2.5 \text{ Vdc}) $ $ (V_{OH} = 4.6 \text{ Vdc}) $ $ (V_{OH} = 9.5 \text{ Vdc}) $ $ (V_{OH} = 13.5 \text{ Vdc}) $	Source	I <sub>OH</sub>	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - - -	-1.7 -0.36 -0.9 -2.4	- - - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		l <sub>in</sub>	15	-	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	-	-	_	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	0.25 0.5 1.0	- - -	0.0005 0.0010 0.0015	0.25 0.5 1.0	- - -	7.5 15 30	μAdc
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Gate, C <sub>L</sub> = 50 pF)		I <sub>T</sub>	5.0 10 15			$I_{T} = (0.$	3 μΑ/kHz) f - 6 μΑ/kHz) f - 9 μΑ/kHz) f -	+ I <sub>DD</sub> /N		•	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.
 To calculate total supply current at loads other than 50 pF:

### SWITCHING CHARACTERISTICS (Note 5) (C $_L$ = 50 pF, $T_A$ = $25^{\circ}C)$

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) \text{ C}_L + 33 \text{ ns} \\ t_{TLH} = (0.60 \text{ ns/pF}) \text{ C}_L + 20 \text{ ns} \\ t_{TLH} = (0.40 \text{ ns/PF}) \text{ C}_L + 20 \text{ ns}$	t <sub>TLH</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) \text{ C}_L + 33 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) \text{ C}_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) \text{ C}_L + 20 \text{ ns}$	t <sub>THL</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH},t_{PHL}=(0.90\;\text{ns/pF})\;C_L+115\;\text{ns}$ $t_{PLH},t_{PHL}=(0.36\;\text{ns/pF})\;C_L+47\;\text{ns}$ $t_{PLH},t_{PHL}=(0.26\;\text{ns/pF})\;C_L+37\;\text{ns}$	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0 10 15	- - -	160 65 50	300 130 100	ns

- 5. The formulas given are for the typical characteristics only at 25°C.
  6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

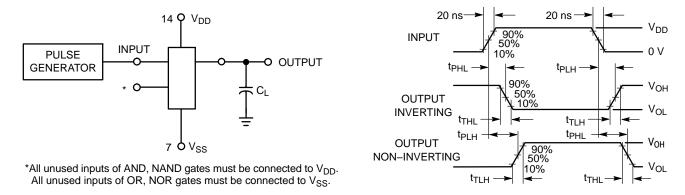


Figure 3. Switching Time Test Circuit and Waveforms

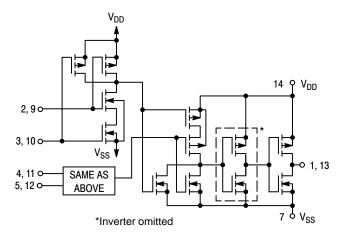


Figure 4. Circuit Schematic - One of Two Gates Shown

#### TYPICAL B-SERIES GATE CHARACTERISTICS

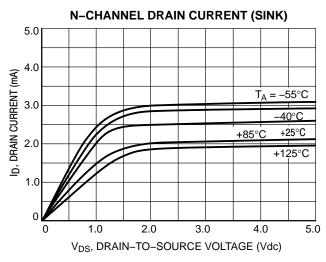


Figure 5.  $V_{GS} = 5.0 \text{ Vdc}$ 

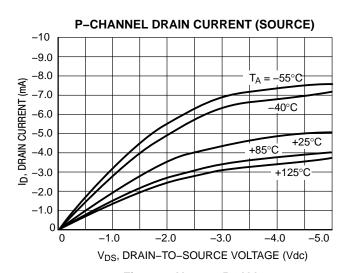


Figure 6.  $V_{GS} = -5.0 \text{ Vdc}$ 

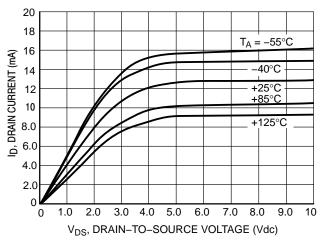


Figure 7. V<sub>GS</sub> = 10 Vdc

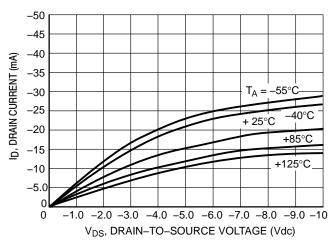


Figure 8.  $V_{GS} = -10 \text{ Vdc}$ 

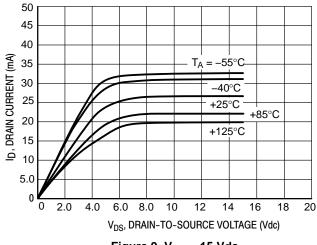


Figure 9.  $V_{GS} = 15 \text{ Vdc}$ 

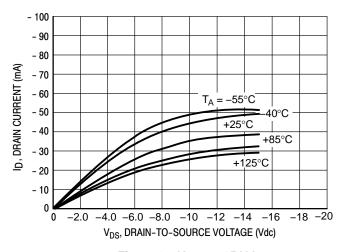


Figure 10.  $V_{GS} = -15 \text{ Vdc}$ 

These typical curves are not guarantees, but are design aids. Caution: The maximum rating for output current is 10 mA per pin.

#### **VOLTAGE TRANSFER CHARACTERISTICS**

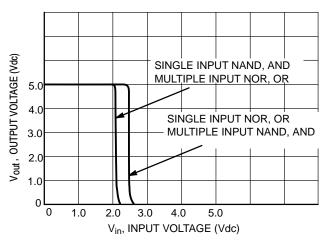


Figure 11.  $V_{DD} = 5.0 \text{ Vdc}$ 

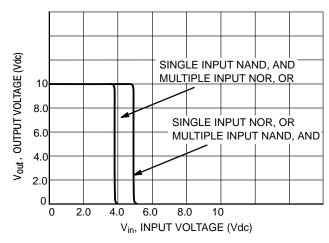


Figure 12. V<sub>DD</sub> = 10 Vdc

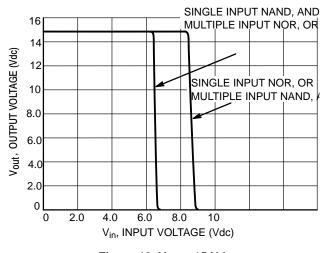


Figure 13.  $V_{DD} = 15 \text{ Vdc}$ 

#### DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal "1" or "0" input level which does not produce output state change(s). The typical and guaranteed limit values of the input values  $V_{IL}$  and  $V_{IH}$  for the output(s) to be at a fixed voltage  $V_O$  are given in the Electrical Characteristics table.  $V_{IL}$  and  $V_{IH}$  are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the "1" and "0" levels =

1.0 V with a 5.0 V supply

2.0 V with a 10.0 V supply

2.5 V with a 15.0 V supply

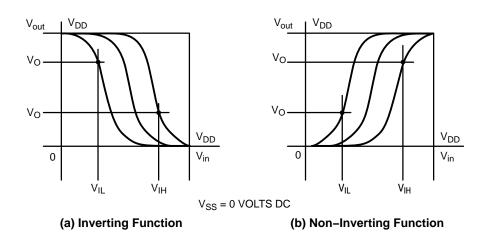


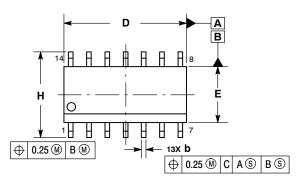
Figure 14. DC Noise Immunity



△ 0.10

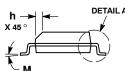
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
  - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
œ	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7 °

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

# **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

C SEATING PLANE

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2		

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### SOIC-14 CASE 751A-03 ISSUE L

### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2		

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

# onsemi:

<u>MC14012BCP MC14012BCPG MC14012BD MC14012BDG MC14012BDR2 MC14012BDR2G </u>